

# N-channel 30 V 3.4 mΩ logic level MOSFET Rev. 01 — 2 November 2010

Product data sheet

#### **Product profile** 1.

#### **1.1 General description**

Logic level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- **1.3 Applications** 
  - DC-to-DC converters
  - Load switching

- Suitable for logic level gate drive sources
- Motor control
- Server power supplies

#### 1.4 Quick reference data

#### Table 1. **Quick reference data**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u>	<u>[1]</u>	-	-	100	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	114	W
Tj	junction temperature			-55	-	175	°C
Static character	ristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 10 \text{ A};$ T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	3.5	4.1	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	[2]	-	2.8	3.4	mΩ
Dynamic chara	cteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 25 A;		-	8	-	nC
Q <sub>G(tot)</sub>	total gate charge	$V_{DS} = 15 V$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>		-	31	-	nC
Avalanche rugg	jedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} V_{GS} &= 10 \text{ V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \\ \text{I}_{D} &= 100  \text{A};  \text{V}_{sup} \leq 30  \text{V}; \\ \text{R}_{GS} &= 50  \Omega; \text{ unclamped} \end{split} $		-	-	200	mJ

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- [1] Continuous current is limited by package.
- [2] Measured 3 mm from package.

### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT78 (TO-220AB)

### 3. Ordering information

Table 3.         Ordering information					
Type number	Package				
	Name	Description	Version		
PSMN3R4-30PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78		

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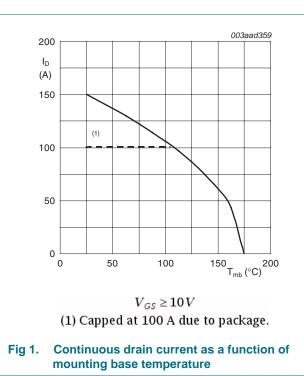
### 4. Limiting values

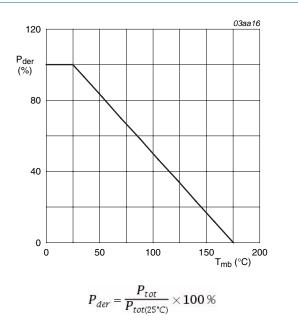
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	30	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ		-	30	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	[1]	-	100	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	[1]	-	100	А
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 µs; T <sub>mb</sub> = 25 °C; see <u>Figure 3</u>		-	609	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	114	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	100	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	609	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^\circ \! C; \; I_D = 100 \; A; \\ V_{sup} \leq 30 \; V; \; R_{GS} = 50 \; \Omega; \; unclamped \end{array} $		-	200	mJ

[1] Continuous current is limited by package.

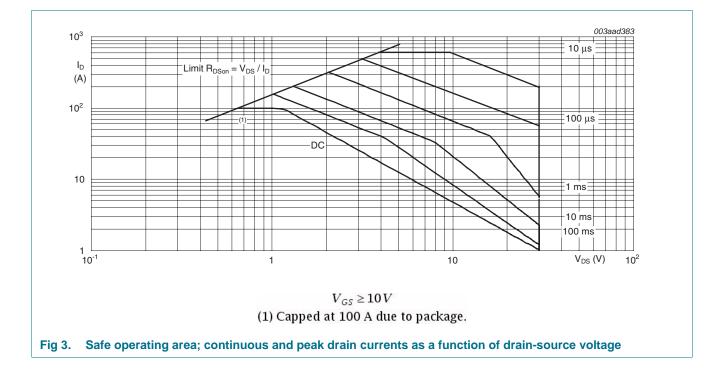






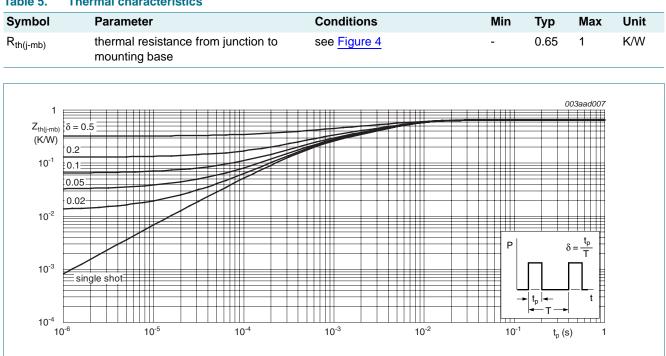
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### 5. Thermal characteristics



#### Table 5. Thermal characteristics

Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

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### 6. Characteristics

#### Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
		$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
V <sub>GS(th)</sub> gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	1.3	1.7	2.15	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 11	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 11</u>	-	-	2.45	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V};  V_{GS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	0.3	5	μΑ
		$V_{DS} = 30 \text{ V};  V_{GS} = 0 \text{ V};  T_j = 125 ^{\circ}\text{C}$	-	-	100	μΑ
I <sub>GSS</sub> gate leakage current	gate leakage current	$V_{GS}$ = 16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS} = -16 \text{ V};  V_{DS} = 0 \text{ V};  T_j = 25 ^{\circ}\text{C}$	-	10	100	nA
R <sub>DSon</sub> drain-source on-state resistance	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 175 °C; see <u>Figure 12</u>	-	-	6.46	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 10 A; $T_j$ = 25 °C; see Figure 13	-	3.5	4.1	mΩ
	$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 100 °C; see <u>Figure 12</u>	-	-	6.1	mΩ	
	$V_{GS}$ = 4.5 V; $I_D$ = 10 A; $T_j$ = 175 °C; see <u>Figure 12</u>	-	-	7.79	mΩ	
	$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 25 °C; see Figure 13	<u>[1]</u> _	2.8	3.4	mΩ	
R <sub>G</sub>	gate resistance	f = 1 MHz	-	1	-	Ω
Dynamic cha	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	64	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	58	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	31	-	nC
Q <sub>GS</sub>	gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	12	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	6.2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	5.8	-	nC
Q <sub>GD</sub>	gate-drain charge		-	8	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 15 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	2.8	-	V
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 12 V; $V_{GS}$ = 0 V; f = 1 MHz;	-	3907	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 16$	-	822	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	356	-	pF

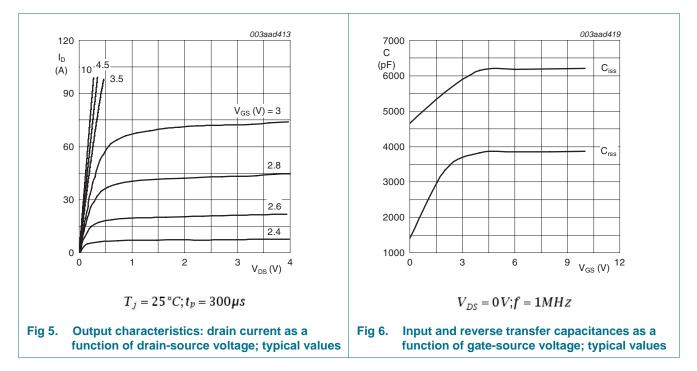
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#### Table 6. Characteristics ...continued

Tested to JEDEC standards where applicable.

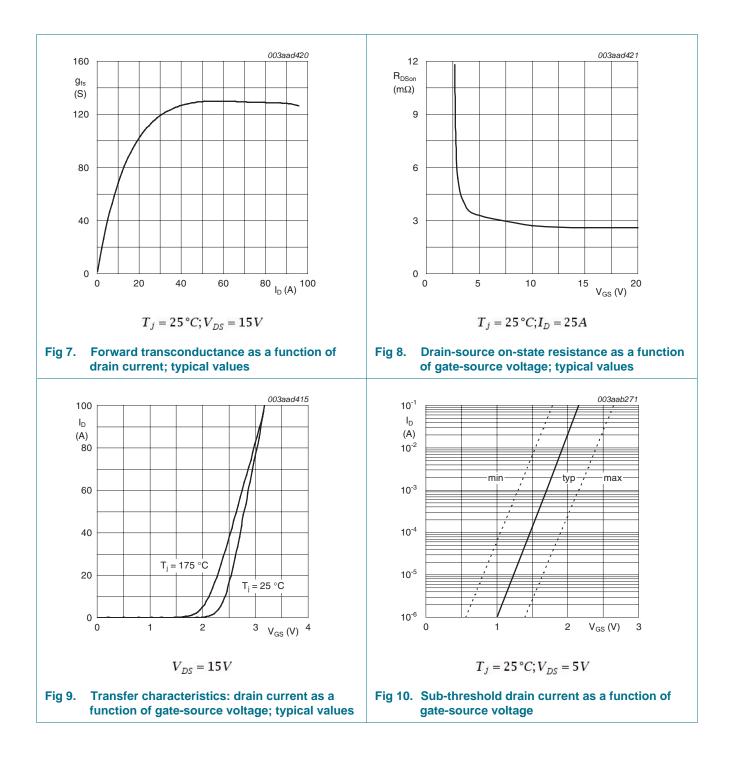
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>d(on)</sub>	turn-on delay time		-	40	-	ns
t <sub>r</sub>	rise time		-	73	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	59	-	ns
t <sub>f</sub>	fall time		-	28	-	ns
Source-drai	n diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 10 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.7	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	36	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 V; V_{DS} = 12 V$	-	28	-	nC

[1] Measured 3 mm from package.



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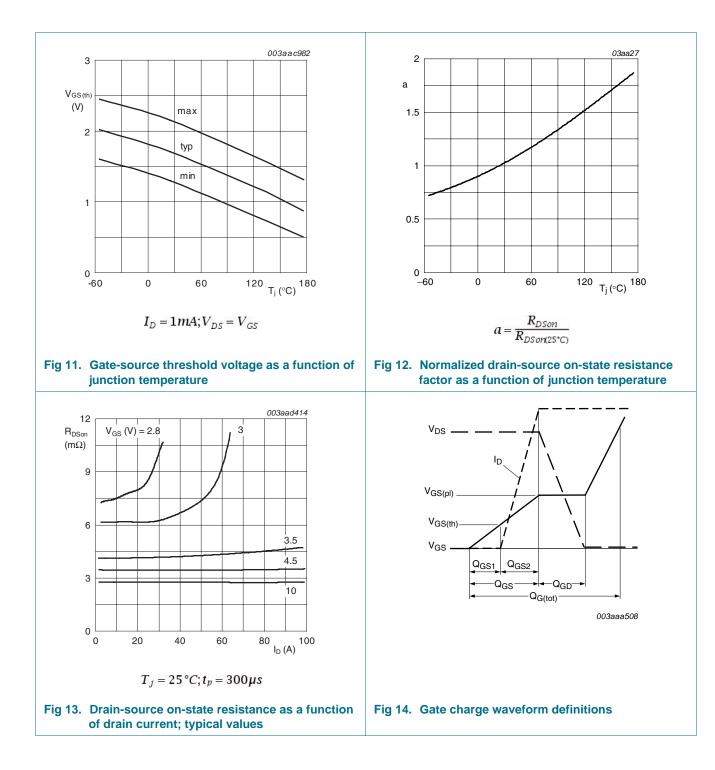


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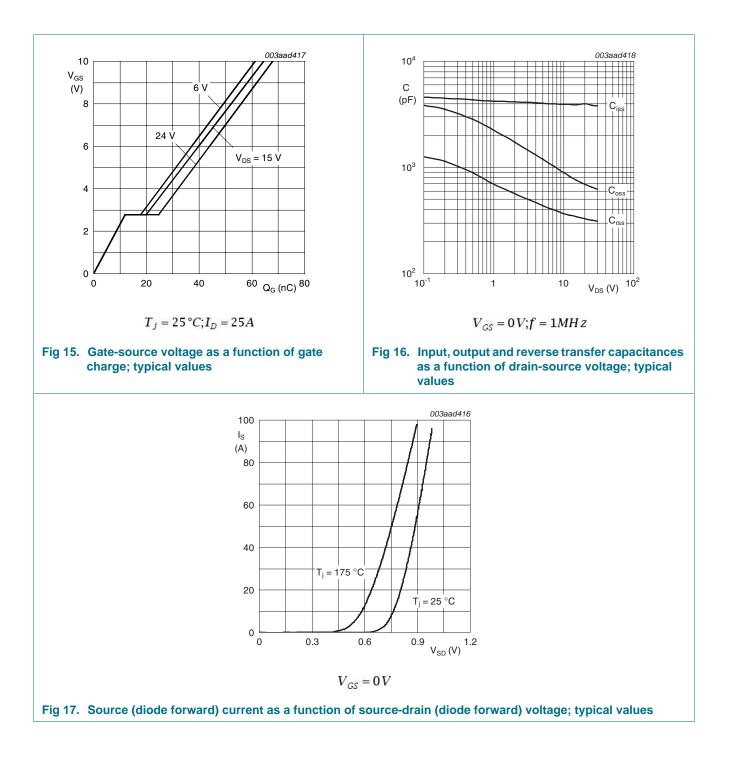
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#### **Package outline** 7.

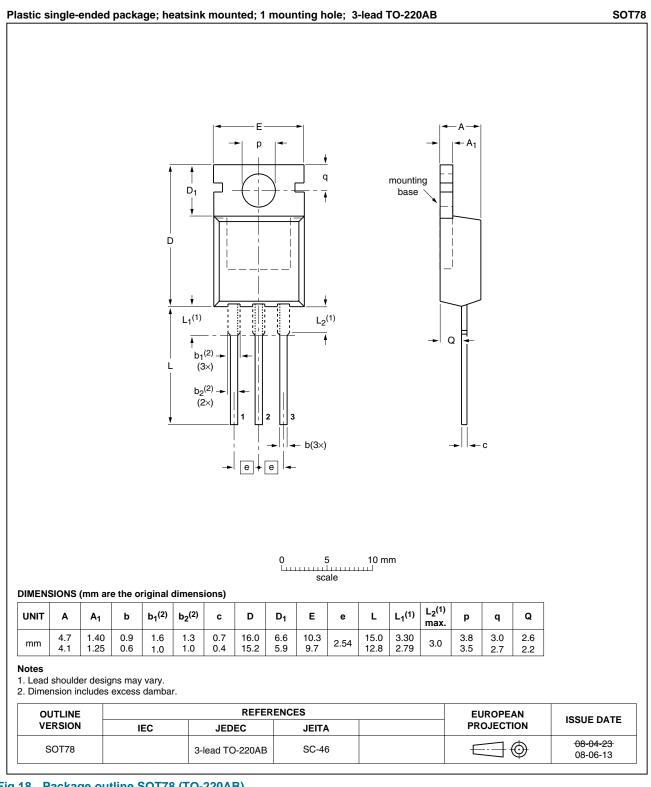


Fig 18. Package outline SOT78 (TO-220AB)

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### 8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R4-30PL v.1	20101102	Product data sheet	-	-

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### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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